ABSTRACT OF THE DISCLOSURE

An object of the present invention is to provide a semiconductor laser device which is capable of selectively emitting two kinds of laser light of light emitting characteristics differing in wavelength, light emission point, beam shape, light emission power, longitudinal mode and so on, by switching the direction of the voltage applied to the device. There is provided the semiconductor laser device including first and second laser units, each unit having a ridge type structure and each unit comprising a multilayer structure body made of at least an n-type semiconductor layer, an active layer and a p-type semiconductor layer deposited in this order, and a p-side electrode and an n-side electrode, wherein the p-side electrode and the n-side electrode of the first laser unit and the n-side electrode and the p-side electrode of the second laser unit are electrically connected, respectively.